

The cited references disclose an optical mask in contact with the substrate to be irradiated with light. In contrast, the optical mask recited in claims 1 and 7 is separated from the substrate so that the light can project the pattern on the substrate through the optical mask.

Attached is a marked-up version of the changes made to the claims by the current amendment. The attached pages are captioned **“Version With Marks To Show Changes Made”**.

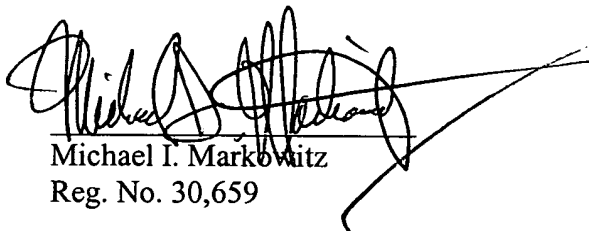
CLOSING

An earnest effort has been made to be fully responsive to the Examiner's objections. In view of the above amendments and remarks, it is believed that independent claims 1 and 7 are in condition for allowance, as well as those claims dependent therefrom. Passage of this case to allowance is earnestly solicited.

However, if for any reason the Examiner should consider this application not to be in condition for allowance, he is respectfully requested to telephone the undersigned attorney at the number listed below prior to issuing a further Action.

Any fee due with this paper, not fully covered by an enclosed check, may be charged on Deposit Account 50-1290.

Respectfully submitted,



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Enclosure: Version With Markings to Show Changes Made

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS

Claims 1 and 7 have been rewritten as follows:

1. (Twice Amended) A method for forming a first-property semiconductor film at a desired position on a substrate, comprising the steps of:

- a) preparing the substrate having a second-property semiconductor film formed thereon;
- b) preparing an optical mask having a predetermined [pattern;] pattern on another substrate which is apart from the substrate;
- c) relatively positioning a projection area of the optical mask at the desired position on the substrate;
- d) irradiating the desired position of the second-property semiconductor film with laser light through the optical mask to change an irradiated portion of the second-property semiconductor film to the first-property semiconductor film; and
- e) forming an insulation film on the first-property semiconductor film and the second-property semiconductor film.

7. (Twice Amended) A method for forming a crystalline semiconductor film at a desired position on a substrate, comprising the steps of:

- a) preparing the substrate having an amorphous semiconductor film formed thereon;
- b) preparing an optical mask having a predetermined [pattern;] pattern on another substrate which is apart from the substrate;
- c) relatively positioning a projection area of the optical mask at the desired position on the substrate;
- d) irradiating the desired position of the amorphous semiconductor film with laser light through the optical mask to change an irradiated portion of the amorphous semiconductor film to the crystalline semiconductor film; and
- e) forming an insulation film on the crystalline semiconductor film and the amorphous semiconductor film.